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***Pro Hac Vice Applications to follow*

Attorneys for Plaintiff
THIRD DIMENSION SEMICONDUCTOR, INC.

UNITED STATES DISTRICT COURT
NORTHERN DISTRICT OF CALIFORNIA

THIRD DIMENSION SEMICONDUCTOR,
INC.,

Plaintiff,
vs.

ROHM SEMICONDUCTOR U.S.A.,
LLC, ROHM COMPANY, LTD., AND
ROHM USA, INC.

Defendants.

ADR

Filed

APR 27 2012

E-filing

RICHARD W. WIEKING
CLERK, U.S. DISTRICT COURT
NORTHERN DISTRICT OF CALIFORNIA
SAN JOSE

HRL

Case No. **CV 12-02132**

**PLAINTIFF THIRD DIMENSION
SEMICONDUCTOR, INC.'S ORIGINAL
COMPLAINT**

JURY TRIAL DEMANDED

1 Plaintiff Third Dimension Semiconductor, Inc. by and through their undersigned counsel,
2 file this Original Complaint against Defendants Rohm Company, Ltd., Rohm USA, Inc., and
3 Rohm Semiconductor U.S.A., LLC, (collectively "**Defendants**") as follows:

4 **THE PARTIES**

5 1. Plaintiff Third Dimension Semiconductor, Inc. ("**3D Semiconductor**") is a Texas
6 corporation that maintains a principal place of business at 7855 South River Parkway, Suite 122,
7 Tempe, Arizona 85284.

8 2. Upon information and belief, Rohm Semiconductor U.S.A., LLC, is a Delaware
9 corporation with its USA Design Center and Sales Office at 785 N. Mary Avenue, Suite 120,
10 Sunnyvale, CA 94085 and its headquarters at 6815 Flanders Drive Suite #150, San Diego, CA
11 92121. Upon information and belief, Rohm Semiconductor U.S.A., LLC, may be served with
12 process by serving its registered agent, Corporation Service Company, 2730 Gateway Oaks Dr.
13 Suite # 100, Sacramento, CA 95833. Upon information and belief, Rohm Semiconductor U.S.A.,
14 LLC, is a subsidiary of Rohm Company, Ltd. Upon information and belief, Rohm
15 Semiconductor U.S.A., LLC, has conducted and regularly conducts business within this District,
16 has purposefully availed itself of the privileges of conducting business in this District, and has
17 sought protection and benefit from the laws of the State of California.

18 3. Upon information and belief, Rohm Company, Ltd., is a Japanese company with
19 its principal place of business at 21 Saiin Mizosaki-cho, Ukyo-ku, Kyoto 615-8585, Japan. Upon
20 information and belief, Rohm Company, Ltd. may be served with process in Japan pursuant to
21 the Hague Convention on the Service Abroad of Judicial and Extrajudicial Documents in Civil or
22 Commercial Matters. Upon information and belief, Rohm Company, Ltd. has conducted and
23 regularly conducts business within this District, has purposefully availed itself of the privileges
24 of conducting business in this District, and has sought protection and benefit from the laws of the
25 State of California by directing and/or controlling the actions of its subsidiaries, Rohm
26 Semiconductor U.S.A., LLC and Rohm USA, Inc.

1 4. Upon information and belief, Rohm USA, Inc. is a Delaware corporation with its
2 principal place of business at 6815 Flanders Drive Suite #150, San Diego, CA 92121. Upon
3 information and belief, Rohm Semiconductor USA may be served with process by serving its
4 registered agent, Corporation Service Company, 2730 Gateway Oaks Dr. Suite # 100,
5 Sacramento, CA 95833. Upon information and belief, Rohm USA, Inc. is a subsidiary of Rohm
6 Company, Ltd. Upon information and belief, Rohm USA, Inc. has conducted and regularly
7 conducts business within this District, has purposefully availed itself of the privileges of
8 conducting business in this District, and has sought protection and benefit from the laws of the
9 State of California.

10 **JURISDICTION AND VENUE**

11 5. This action arises under the Patent Laws of the United States, 35 U.S.C. § 1, et
12 seq., including 35 U.S.C. §§ 271, 281, 283, 284, and 285. This Court has subject matter
13 jurisdiction over this case for patent infringement under 28 U.S.C. §§ 1331 and 1338(a).

14 6. As further detailed herein, this Court has personal jurisdiction over each
15 Defendant. Each Defendant has contacts and offices in this District. Each Defendant has
16 conducted and regularly conducts business within the United States and this District. Each
17 Defendant has purposefully availed itself of the privileges of conducting business in the United
18 States, and more specifically in this District. Each Defendant has sought protection and benefit
19 from the laws of the State of California by placing infringing products into the stream of
20 commerce through an established distribution channel with the expectation and/or knowledge
21 that they will be purchased by consumers in this District. Plaintiff's cause of action arises
22 directly from Defendants' business contacts and other activities in this District.

23 7. Each Defendant, directly or through intermediaries (including distributors,
24 retailers, and others), subsidiaries, alter egos, and/or agents, ships, distributes, offers for sale,
25 and/or sells its products in the United States and this District. Each Defendant has purposefully
26 and voluntarily placed one or more of its infringing products, as described below, into the stream
27 of commerce with the expectation and/or knowledge that they will be purchased by consumers in
28

1 this District. Each Defendant knowingly and purposefully ships infringing products into this
2 District through an established distribution channel. These infringing products have been and
3 continue to be purchased by consumers in this District. Upon information and belief, each
4 Defendant has committed the tort of patent infringement in this District.

5 8. Venue is proper in this Court under 28 U.S.C. §§ 1391(b), (c), and (d), as well as
6 28 U.S.C. § 1400(b), in that, upon information and belief, each Defendant has committed acts
7 within this judicial District giving rise to this action and does business in this District, including
8 but not limited to making sales in this District, providing service and support to their respective
9 customers in this District, and/or operating an interactive website that is available to persons in
10 this District, which website advertises, markets, and/or offers for sale infringing products.

11 **INTRADISTRICT ASSIGNMENT**

12 9. Intradistrict Assignment is appropriate under Civil Local Rule 3-2(c) because this
13 is an Intellectual Property Action.

14 **BACKGROUND**

15 **A. The Patents-In-Suit.**

16 10. U.S. Patent No. 5,216,275, titled "Semiconductor Power Devices with Alternating
17 Conductivity Type High-Voltage Breakdown Regions," ("the '**275 patent**'") was duly and legally
18 issued by the U.S. Patent and Trademark Office on June 1, 1993, after full and fair examination.
19 Xingbi Chen is the sole inventor listed on the '275 patent, which was assigned to the University
20 of Electronic Science and Technology of China. In 2001, Dr. Chen and the University assigned
21 their rights and interests in the '275 patent to Power MOSFET Technologies. In 2002, Power
22 MOSFET Technologies assigned its interests in the '275 patent to Plaintiff 3D Semiconductor. A
23 true and correct copy of the '275 patent is attached as **Exhibit A** and made a part hereof.

24 11. U.S. Patent No. 6,635,906, titled "Voltage Sustaining Layer with Opposite-Doped
25 Islands for Semiconductor Power Devices," ("the '**906 patent**'") was duly and legally issued by
26 the U.S. Patent and Trademark Office on October 21, 2003, after full and fair examination.
27 Xingbi Chen is the sole inventor listed on the '906 patent, which was assigned to 3D
28

1 Semiconductor. A true and correct copy of the '906 patent is attached as **Exhibit B** and made a
2 part hereof.

3 12. U.S. Patent No. 6,936,867, titled "Semiconductor High-Voltage Devices," ("the
4 '**867 patent**'") was duly and legally issued by the U.S. Patent and Trademark Office on August
5 30, 2005, after full and fair examination. Xingbi Chen is the sole inventor listed on the '867
6 patent, which was assigned to 3D Semiconductor. A true and correct copy of the '867 patent is
7 attached as **Exhibit C** and made a part hereof.

8 13. U.S. Patent No. 7,271,067, titled "Voltage Sustaining Layer with Opposite-Doped
9 Islands for Semiconductor Power Devices," ("the '**067 patent**'") was duly and legally issued by
10 the U.S. Patent and Trademark Office on September 18, 2007, after full and fair examination.
11 Xingbi Chen is the sole inventor listed on the '067 patent, which was assigned to 3D
12 Semiconductor. A true and correct copy of the '067 patent is attached as **Exhibit D** and made a
13 part hereof.

14 14. U.S. Patent No. 7,439,583, titled "Tungsten Plug Drain Extension," ("the '**583**
15 **patent**'") was duly and legally issued by the U.S. Patent and Trademark Office on October 21,
16 2008, after full and fair examination. Fwu-Iuan Hsieh is the sole inventor listed on the '583
17 patent, which was assigned to 3D Semiconductor. A true and correct copy of the '583 patent is
18 attached as **Exhibit E** and made a part hereof.

19 15. U.S. Patent No. 8,071,450, titled "Method for Forming Voltage Sustaining Layer
20 with Opposite-Doped Islands for Semiconductor Power Devices," ("the '**450 patent**'") was duly
21 and legally issued by the U.S. Patent and Trademark Office on December 6, 2011, after full and
22 fair examination. Xingbi Chen is the sole inventor listed on the '450 patent, which was assigned
23 to 3D Semiconductor. A true and correct copy of the '450 patent is attached as **Exhibit F** and
24 made a part hereof.

25 **B. Defendants' Infringing Conduct.**

26 16. Upon information and belief, Defendants collectively make, use, offer to sell,
27 and/or sell within, and/or import into the United States semiconductor devices that utilize
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1 technologies covered by the patents-in-suit. Upon information and belief, the infringing
2 semiconductor devices include, but are not limited to, metal-oxide-semiconductor field-effect
3 transistors ("**MOSFETs**") with high drain-source voltage and low drain-source resistance
4 ("**RDS(ON)**"). Upon information and belief, customers of Defendants incorporate these
5 semiconductor devices into products that are made, used, offered for sale, and/or sold within,
6 and/or imported into the United States, including this District.

7 17. Since at least December 2009, 3D Semiconductor has met multiple times with
8 Defendants regarding licensing 3D Semiconductor's patents, during which the parties discussed
9 specific examples of Rohm's MOSFETs and 3D Semiconductor's patents.

10 **COUNT I**

11 **Patent Infringement of U.S. Patent No. 5,216,275**

12 18. Plaintiff repeats and re-alleges each and every allegation of paragraphs 1-17 as
13 though fully set forth herein.

14 19. The '275 patent is valid and enforceable.

15 20. Defendants have at no time, either expressly or impliedly, been licensed under the
16 '275 patent.

17 21. Upon information and belief, to the extent any marking or notice was required by
18 35 U.S.C. § 287, Plaintiff has complied with the requirements of that statute by providing actual
19 or constructive notice to Defendants of their alleged infringement. Upon information and belief,
20 Plaintiff surmises that any express licensees of the '275 patent have complied with the marking
21 requirements of 35 U.S.C. § 287 by placing a notice of the '275 patent on all goods made,
22 offered for sale, and/or sold within, and/or imported into, the United States that embody one or
23 more claims of that patent.

24 22. Upon information and belief, Defendants have been directly and literally
25 infringing under 35 U.S.C. § 271(a), the '275 patent by making, using, offering to sell, and/or
26 selling to customers and/or distributors (directly or through intermediaries and/or subsidiaries) in
27 this District and elsewhere within the United States and/or importing into the United States,
28

1 without authority, products containing semiconductor devices that include all of the limitations
2 of one or more claims of the '275 patent, including, but not limited to, MOSFET R6015ANX
3 and other similar products, such as Defendants' high drain-source voltage MOSFETs with low
4 RDS(ON): R8002ANX, R8008ANX, R8005ANX, R6006AND, R6006ANX, R6008ANX,
5 R6008FNJ, R6008FNX, R6010ANX, R6012ANJ, R6012ANX, R6012FNX, R6015ANJ,
6 R6015ANZ, R6015FNX, R6018ANJ, R6018ANX, R6020ANJ, R6020ANX, R6020ANZ,
7 R6020FNX, R6025ANZ, R6046ANZ, R6046FNZ, ZDS020N60, R6004CND, R5205CND,
8 R5207AND, R5005CNJ, R5005CNX, R5007ANJ, R5007ANX, R5009ANJ, R5009ANX,
9 R5009FNX, R5011ANJ, R5011ANX, R5011FNX, R5013ANJ, R5013ANX, R5016ANJ,
10 R5016ANX, R5016FNX, R5019ANJ, R5019ANX, R5021ANJ, R5021ANX, ZDX130N50,
11 RDD022N50, R4008AND, RCD040N25, RCD060N25, RCD080N25, RCJ330N25,
12 RCX050N25, RCX080N25, RCX100N25, RCX120N25, RCX330N25, RCX510N25,
13 RDR005N25, RCJ220N25, RCX220N25, RCD050N20, RCD075N20, RCD100N20,
14 RCJ450N20, RCX080N20, RCX120N20, RCX160N20, RCX450N20, RCX200N20,
15 RCX300N20, RCJ200N20, RCJ300N20, RSD050N10, RSD100N10, RSD175N10,
16 RSD200N10, RSJ300N10, RSJ550N10, RSJ650N10, RSR010N10, and RSJ400N10
17 (collectively, "**Rohm High Voltage MOSFETs**").

18 23. Upon information and belief, Defendants have been directly and equivalently
19 infringing under the doctrine of equivalents, the '275 patent by making, using, offering to sell,
20 and/or selling to customers and/or distributors (directly or through intermediaries and/or
21 subsidiaries) in this District and elsewhere within the United States and/or importing into the
22 United States, without authority, products containing semiconductor devices that include all of
23 the limitations of one or more claims of the '275 patent, including, but not limited to, MOSFET
24 R6015ANX and other similar products. The products containing these semiconductor devices
25 perform substantially the same function as the inventions embodied in one or more claims of the
26 '275 patent in substantially the same way to achieve the same result.

24. Upon information and belief, Defendants' acts of infringement of the '275 patent have been willful and intentional throughout the entire period of its infringing conduct or at least after licensing meetings with 3D Semiconductor, when Defendants were formally placed on notice of infringement.

25. As a direct and proximate result of these acts of patent infringement, Defendants have encroached on the exclusive rights of Plaintiff and its licensees to practice the '275 patent, for which Plaintiff is entitled to at least a reasonable royalty.

COUNT II

Patent Infringement of U.S. Patent No. 6,635,906

26. Plaintiff repeats and re-alleges each and every allegation of paragraphs 1-25 as though fully set forth herein.

27. The '906 patent is valid and enforceable.

28. Defendants have at no time, either expressly or impliedly, been licensed under the '906 patent.

29. Upon information and belief, to the extent any marking or notice was required by 35 U.S.C. § 287, Plaintiff has complied with the requirements of that statute by providing actual or constructive notice to Defendants of their alleged infringement. Upon information and belief, Plaintiff surmises that any express licensees of the '906 patent have complied with the marking requirements of 35 U.S.C. § 287 by placing a notice of the '906 patent on all goods made, offered for sale, and/or sold within, and/or imported into, the United States that embody one or more claims of that patent.

30. Upon information and belief, Defendants have been directly and literally infringing under 35 U.S.C. § 271(a), the '906 patent by making, using, offering to sell, and/or selling to customers and/or distributors (directly or through intermediaries and/or subsidiaries) in this District and elsewhere within the United States and/or importing into the United States, without authority, products containing semiconductor devices that include all of the limitations

1 of one or more claims of the '906 patent, including, but not limited to, MOSFET R6015ANX
2 and other similar products, such as the Rohm High Voltage MOSFETs.

3 31. Upon information and belief, Defendants have been directly and equivalently
4 infringing under the doctrine of equivalents, the '906 patent by making, using, offering to sell,
5 and/or selling to customers and/or distributors (directly or through intermediaries and/or
6 subsidiaries) in this District and elsewhere within the United States and/or importing into the
7 United States, without authority, products containing semiconductor devices that include all of
8 the limitations of one or more claims of the '906 patent, including, but not limited to, MOSFET
9 R6015ANX and other similar products. The products containing these semiconductor devices
10 perform substantially the same function as the inventions embodied in one or more claims of the
11 '906 patent in substantially the same way to achieve the same result.

12 32. Upon information and belief, Defendants' acts of infringement of the '906 patent
13 have been willful and intentional throughout the entire period of its infringing conduct or at least
14 after licensing meetings with 3D Semiconductor, when Defendants were formally placed on
15 notice of infringement.

16 33. As a direct and proximate result of these acts of patent infringement, Defendants
17 have encroached on the exclusive rights of Plaintiff and its licensees to practice the '906 patent,
18 for which Plaintiff is entitled to at least a reasonable royalty.

19 **COUNT III**

20 **Patent Infringement of U.S. Patent No. 6,936,867**

21 34. Plaintiff repeats and re-alleges each and every allegation of paragraphs 1-33 as
22 though fully set forth herein.

23 35. The '867 patent is valid and enforceable.

24 36. Defendants have at no time, either expressly or impliedly, been licensed under the
25 '867 patent.

26 37. Upon information and belief, to the extent any marking or notice was required by
27 35 U.S.C. § 287, Plaintiff has complied with the requirements of that statute by providing actual
28

1 or constructive notice to Defendants of their alleged infringement. Upon information and belief,
2 Plaintiff surmises that any express licensees of the '867 patent have complied with the marking
3 requirements of 35 U.S.C. § 287 by placing a notice of the '867 patent on all goods made,
4 offered for sale, and/or sold within, and/or imported into, the United States that embody one or
5 more claims of that patent.

6 38. Upon information and belief, Defendants have been directly and literally
7 infringing under 35 U.S.C. § 271(a), the '867 patent by making, using, offering to sell, and/or
8 selling to customers and/or distributors (directly or through intermediaries and/or subsidiaries) in
9 this District and elsewhere within the United States and/or importing into the United States,
10 without authority, products containing semiconductor devices that include all of the limitations
11 of one or more claims of the '867 patent, including, but not limited to, MOSFET R6015ANX
12 and other similar products, such as the Rohm High Voltage MOSFETs.

13 39. Upon information and belief, Defendants have been directly and equivalently
14 infringing under the doctrine of equivalents, the '867 patent by making, using, offering to sell,
15 and/or selling to customers and/or distributors (directly or through intermediaries and/or
16 subsidiaries) in this District and elsewhere within the United States and/or importing into the
17 United States, without authority, products containing semiconductor devices that include all of
18 the limitations of one or more claims of the '867 patent, including, but not limited to, MOSFET
19 R6015ANX and other similar products. The products containing these semiconductor devices
20 perform substantially the same function as the inventions embodied in one or more claims of the
21 '867 patent in substantially the same way to achieve the same result.

22 40. Upon information and belief, Defendants' acts of infringement of the '867 patent
23 have been willful and intentional throughout the entire period of its infringing conduct or at least
24 after licensing meetings with 3D Semiconductor, when Defendants were formally placed on
25 notice of infringement.

41. As a direct and proximate result of these acts of patent infringement, Defendants have encroached on the exclusive rights of Plaintiff and its licensees to practice the '867 patent, for which Plaintiff is entitled to at least a reasonable royalty.

COUNT IV

Patent Infringement of U.S. Patent No. 7,271,067

42. Plaintiff repeats and re-alleges each and every allegation of paragraphs 1-41 as though fully set forth herein.

43. The '067 patent is valid and enforceable.

44. Defendants have at no time, either expressly or impliedly, been licensed under the '067 patent.

45. Upon information and belief, to the extent any marking or notice was required by 35 U.S.C. § 287, Plaintiff has complied with the requirements of that statute by providing actual or constructive notice to Defendants of their alleged infringement. Upon information and belief, Plaintiff surmises that any express licensees of the '067 patent have complied with the marking requirements of 35 U.S.C. § 287 by placing a notice of the '067 patent on all goods made, offered for sale, and/or sold within, and/or imported into, the United States that embody one or more claims of that patent.

46. Upon information and belief, Defendants have been directly and literally infringing under 35 U.S.C. § 271(a) or (g), the '067 patent by making, using, importing, offering to sell, and/or selling to customers and/or distributors (directly or through intermediaries and/or subsidiaries) in this District and elsewhere within the United States and/or importing into the United States, without authority, semiconductor devices manufactured with all of the limitations of one or more claims of the '067 patent, including, but not limited to, MOSFET R6015ANX and other similar products, such as the Rohm High Voltage MOSFETs.

47. Upon information and belief, Defendants have been directly and equivalently infringing under the doctrine of equivalents, the '067 patent by making, using, offering to sell, and/or selling to customers and/or distributors (directly or through intermediaries and/or

1 subsidiaries) in this District and elsewhere within the United States and/or importing into the
2 United States, without authority, semiconductor manufactured according to the limitations of one
3 or more claims of the '067 patent, including, but not limited to, MOSFET R6015ANX and other
4 similar products. The manufacture of these semiconductor devices perform substantially the
5 same function as the inventions embodied in one or more claims of the '067 patent in
6 substantially the same way to achieve the same result.

7 48. Upon information and belief, Defendants' acts of infringement of the '067 patent
8 have been willful and intentional throughout the entire period of its infringing conduct or at least
9 after licensing meetings with 3D Semiconductor, when Defendants were formally placed on
10 notice of infringement.

11 49. As a direct and proximate result of these acts of patent infringement, Defendants
12 have encroached on the exclusive rights of Plaintiff and its licensees to practice the '067 patent,
13 for which Plaintiff is entitled to at least a reasonable royalty.

14 COUNT V

15 Patent Infringement of U.S. Patent No. 7,439,583

16 50. Plaintiff repeats and re-alleges each and every allegation of paragraphs 1-49 as
17 though fully set forth herein.

18 51. The '583 patent is valid and enforceable.

19 52. Defendants have at no time, either expressly or impliedly, been licensed under the
20 '583 patent.

21 53. Upon information and belief, to the extent any marking or notice was required by
22 35 U.S.C. § 287, Plaintiff has complied with the requirements of that statute by providing actual
23 or constructive notice to Defendants of their alleged infringement. Upon information and belief,
24 Plaintiff surmises that any express licensees of the '583 patent have complied with the marking
25 requirements of 35 U.S.C. § 287 by placing a notice of the '583 patent on all goods made,
26 offered for sale, and/or sold within, and/or imported into, the United States that embody one or
27 more claims of that patent.

54. Upon information and belief, Defendants have been directly and literally infringing under 35 U.S.C. § 271(a), the '583 patent by making, using, offering to sell, and/or selling to customers and/or distributors (directly or through intermediaries and/or subsidiaries) in this District and elsewhere within the United States and/or importing into the United States, without authority, products containing semiconductor devices that include all of the limitations of one or more claims of the '583 patent, including, but not limited to, MOSFET R6015ANX and other similar products, such as the Rohm High Voltage MOSFETs.

55. Upon information and belief, Defendants have been directly and equivalently infringing under the doctrine of equivalents, the '583 patent by making, using, offering to sell, and/or selling to customers and/or distributors (directly or through intermediaries and/or subsidiaries) in this District and elsewhere within the United States and/or importing into the United States, without authority, products containing semiconductor devices that include all of the limitations of one or more claims of the '583 patent, including, but not limited to, MOSFET R6015ANX and other similar products. The products containing these semiconductor devices perform substantially the same function as the inventions embodied in one or more claims of the '583 patent in substantially the same way to achieve the same result.

56. Upon information and belief, Defendants' acts of infringement of the '583 patent have been willful and intentional throughout the entire period of its infringing conduct or at least after licensing meetings with 3D Semiconductor, when Defendants were formally placed on notice of infringement.

57. As a direct and proximate result of these acts of patent infringement, Defendants have encroached on the exclusive rights of Plaintiff and its licensees to practice the '583 patent, for which Plaintiff is entitled to at least a reasonable royalty.

COUNT VI

Patent Infringement of U.S. Patent No. 8,071,450

58. Plaintiff repeats and re-alleges each and every allegation of paragraphs 1-57 as though fully set forth herein.

59. The '450 patent is valid and enforceable.

60. Defendants have at no time, either expressly or impliedly, been licensed under the '450 patent.

61. Upon information and belief, to the extent any marking or notice was required by 35 U.S.C. § 287, Plaintiff has complied with the requirements of that statute by providing actual or constructive notice to Defendants of their alleged infringement. Upon information and belief, Plaintiff surmises that any express licensees of the '450 patent have complied with the marking requirements of 35 U.S.C. § 287 by placing a notice of the '450 patent on all goods made, offered for sale, and/or sold within, and/or imported into, the United States that embody one or more claims of that patent.

62. Upon information and belief, Defendants have been directly and literally infringing under 35 U.S.C. § 271(a) or (g), the '450 patent by making, using, importing, offering to sell, and/or selling to customers and/or distributors (directly or through intermediaries and/or subsidiaries) in this District and elsewhere within the United States and/or importing into the United States, without authority, semiconductor devices manufactured with all of the limitations of one or more claims of the '450 patent, including, but not limited to, MOSFET R6015ANX and other similar products, such as the Rohm High Voltage MOSFETs.

63. Upon information and belief, Defendants have been directly and equivalently infringing under the doctrine of equivalents, the '450 patent by making, using, offering to sell, and/or selling to customers and/or distributors (directly or through intermediaries and/or subsidiaries) in this District and elsewhere within the United States and/or importing into the United States, without authority, semiconductor manufactured according to the limitations of one or more claims of the '450 patent, including, but not limited to, MOSFET R6015ANX and other similar products. The manufacture of these semiconductor devices perform substantially the same function as the inventions embodied in one or more claims of the '450 patent in substantially the same way to achieve the same result.

64. Upon information and belief, Defendants' acts of infringement of the '450 patent have been willful and intentional throughout the entire period of its infringing conduct or at least after licensing meetings with 3D Semiconductor, when Defendants were formally placed on notice of infringement.

65. As a direct and proximate result of these acts of patent infringement, Defendants have encroached on the exclusive rights of Plaintiff and its licensees to practice the '450 patent, for which Plaintiff is entitled to at least a reasonable royalty.

CONCLUSION

66. Plaintiff is entitled to recover from Defendants the damages sustained by Plaintiff as a result of Defendants' wrongful acts in an amount subject to proof at trial, which, by law, cannot be less than a reasonable royalty, together with interest and costs as fixed by this Court.

67. Plaintiff has incurred and will incur attorneys' fees, costs, and expenses in the prosecution of this action. The circumstances of this dispute create an exceptional case within the meaning of 35 U.S.C. § 285, and Plaintiff is entitled to recover their reasonable and necessary attorneys' fees, costs, and expenses.

JURY DEMAND

68. Plaintiff hereby requests a trial by jury pursuant to Rule 38 of the Federal Rules of Civil Procedure.

PRAYER FOR RELIEF

69. Plaintiff respectfully requests that the Court find in their favor and against Defendants, and that the Court grant Plaintiff the following relief:

A. A judgment that each Defendant has infringed the patents-in-suit as alleged herein under 35 U.S.C. § 271;

B. A judgment for an accounting of all damages sustained by Plaintiff as a result of the acts of infringement by each Defendant;

C. A judgment and order requiring each Defendant to pay Plaintiff damages under 35 U.S.C. § 284, and any royalties determined to be appropriate;

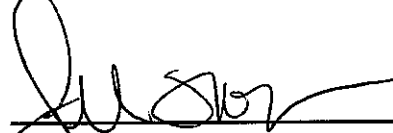
1 D. A judgment and order requiring each Defendant to pay Plaintiff pre-judgment and
2 post-judgment interest on the damages awarded;

3 E. A judgment and order finding this to be an exceptional case and requiring each
4 Defendant to pay the costs of this action (including all disbursements) and attorneys' fees as
5 provided by 35 U.S.C. § 285; and

6 F. Such other and further relief as the Court deems just and equitable.
7

8 Date: April 27, 2012

Respectfully submitted,

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17 ** Pro Hac Vice Applications to Follow
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